

SANYO	No.2458	<h1 style="margin: 0;">2SA1572/2SC4067</h1> <p style="margin: 0;">PNP/NPN Epitaxial Planar Silicon Transistors</p> <h2 style="margin: 0;">Switching Applications</h2> <p style="margin: 0;">(with Bias Resistance)</p>
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Applications

- . Switching circuit, inverter circuit, interface circuit, driver circuit

Features

- . On-chip bias resistance: R1=0, R2=47kΩ
- . Small-sized package: SPA

(): PNP

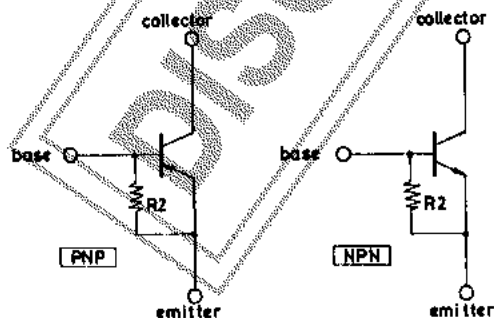
Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V_{CB0}	(-)50	V
Collector to Emitter Voltage	V_{CEO}	(-)50	V
Emitter to Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)100	mA
Collector Current(Pulse)	I_{CP}	(-)200	mA
Collector Dissipation	P_C	300	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

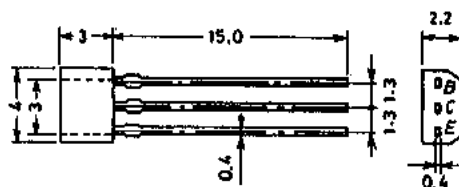
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40V, I_E=0$			(-)0.1	μA
	I_{CEO}	$V_{CE}=(-)40V, I_B=0$			(-)0.5	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)5V, I_C=0$	(-)81	(-)106	(-)151	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)5V, I_C=(-)10mA$	80			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10V, I_C=(-)5mA$		250		MHz
				(200)		
Output Capacitance	c_{ob}	$V_{CB}=(-)10V, f=1MHz$		3.7		pF
				(5.5)		
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)10mA, I_B=(-)0.5mA$			(-)0.1(-)0.3	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)50			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)100\mu A, R_{BE}=\infty$	(-)50			V
Resistance	R2		33	47	61	kΩ

Electrical Connection



Case Outline 2033
(unit:mm)



B: Base
C: Collector
E: Emitter
SANYO: SPA

Specifications and information herein are subject to change without notice.

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